

**HIGH EFFICIENCY ULTRAFAST DIODE**
**MAIN PRODUCT CHARACTERISTICS**

<b>I<sub>F(AV)</sub></b>	<b>1 A</b>
<b>V<sub>RRM</sub></b>	<b>200 V</b>
<b>T<sub>j</sub> (max)</b>	<b>175 °C</b>
<b>V<sub>F</sub> (max)</b>	<b>0.78 V</b>
<b>t<sub>rr</sub> (max)</b>	<b>20 ns</b>

**FEATURES AND BENEFITS**

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times
- High junction temperature

**DESCRIPTION**

The STTH102, which is using ST's new 200V planar technology, is specially suited for switching mode base drive & transistor circuits.

The device is also intended for use as a free wheeling diode in power supplies and other power switching applications.


**ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter		Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage		200	V
I <sub>F(AV)</sub>	Average forward current	T <sub>I</sub> = 130°C    δ = 0.5	1	A
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms    Sinusoidal	50	A
T <sub>stg</sub>	Storage temperature range		- 65 + 175	°C
T <sub>j</sub>	Maximum operating junction temperature		+ 175	°C

**THERMAL PARAMETERS**

Symbol	Parameter	Maximum	Unit
R <sub>th(j-a)</sub>	Junction to ambient*	50	°C/W

\* On infinite heatsink with 10mm length.

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> *	Reverse leakage current	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			1	μA
		T <sub>j</sub> = 125°C			1	25	
V <sub>F</sub> **	Forward voltage drop	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A			0.97	V
		T <sub>j</sub> = 125°C			0.68	0.78	

Pulse test: \* tp = 5ms, δ < 2%

\*\* tp = 380μs, δ < 2%

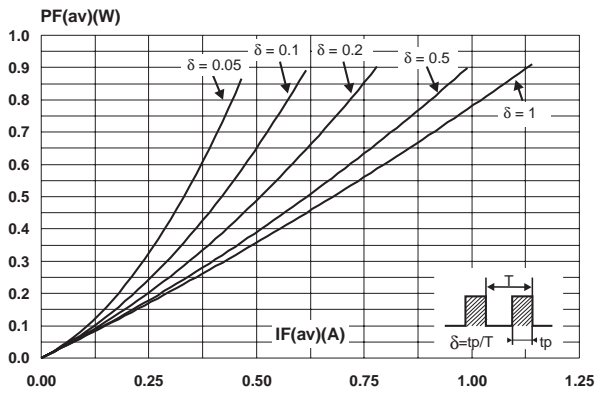
To evaluate the maximum conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.130 \times I_{F(RMS)}^2$$

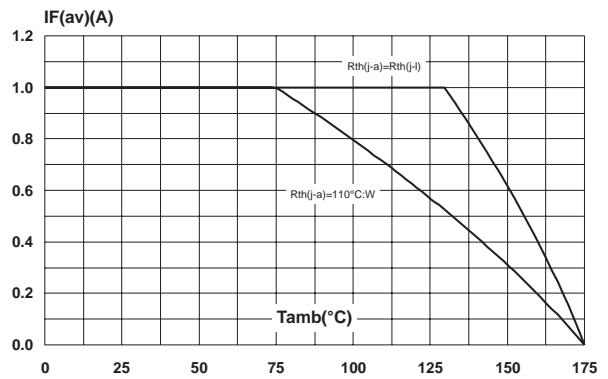
**DYNAMIC ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
trr	Reverse recovery time	I <sub>F</sub> = 0.5 A I <sub>rr</sub> = 0.25 A I <sub>R</sub> = 1A	T <sub>j</sub> = 25°C		12	20	ns
tfr	Forward recovery time	I <sub>F</sub> = 1 A dI <sub>F</sub> /dt = 50A/μs V <sub>FR</sub> = 1.1 x V <sub>Fmax</sub>	T <sub>j</sub> = 25°C		50		ns
V <sub>FP</sub>	Forward recovery voltage		T <sub>j</sub> = 25°C		1.8		V

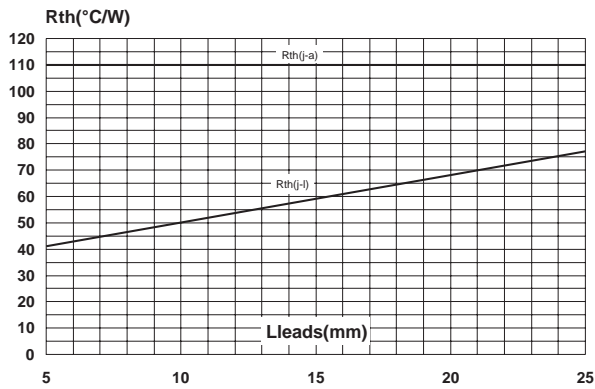
**Fig. 1:** Average forward power dissipation versus average forward current.



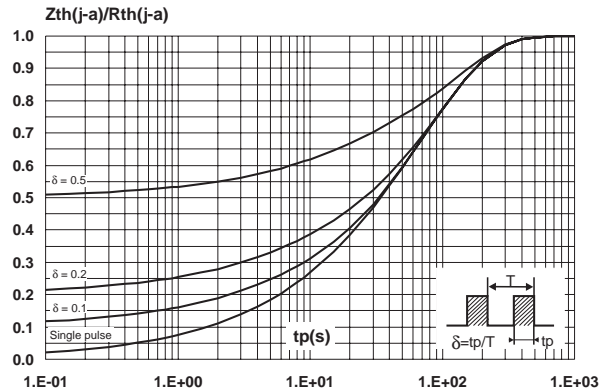
**Fig. 2:** Average forward current versus ambient temperature ( $\delta = 0.5$ ).



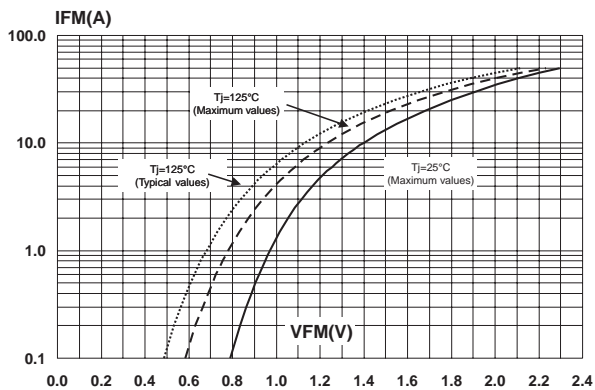
**Fig. 3:** Thermal resistance versus lead length.



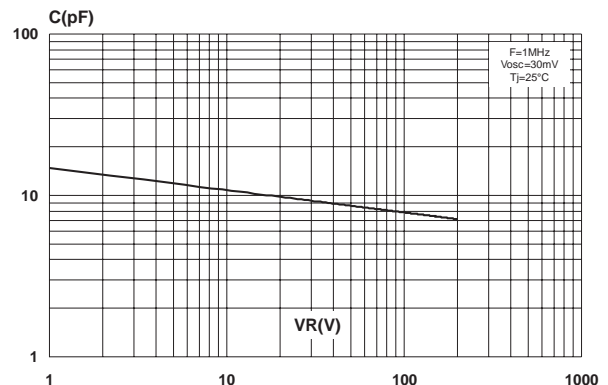
**Fig. 4:** Relative variation of thermal impedance junction ambient versus pulse duration (Printed circuit board epoxy FR4, Leads = 10mm).



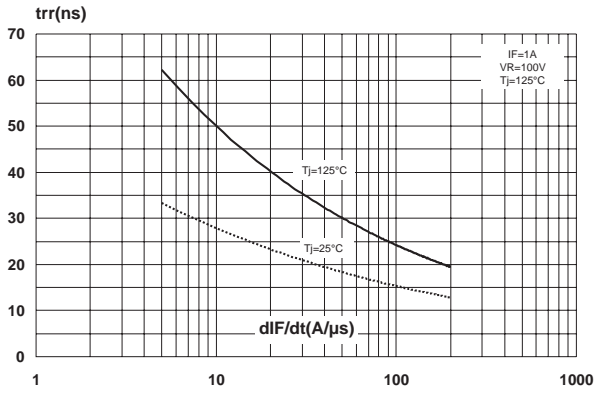
**Fig. 5:** Forward voltage drop versus forward current.



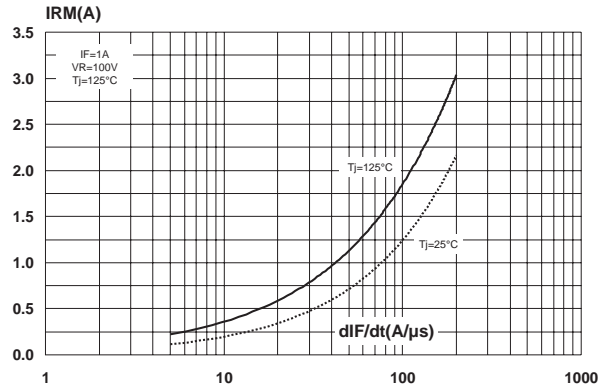
**Fig. 6:** Junction capacitance versus reverse voltage applied (typical values).



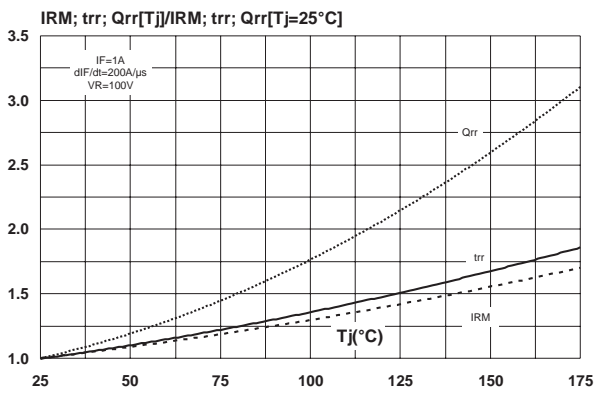
**Fig. 7:** Reverse recovery time versus  $dI/dt$  (90% confidence).



**Fig. 8:** Peak reverse recovery current versus  $dI/dt$  (90% confidence).

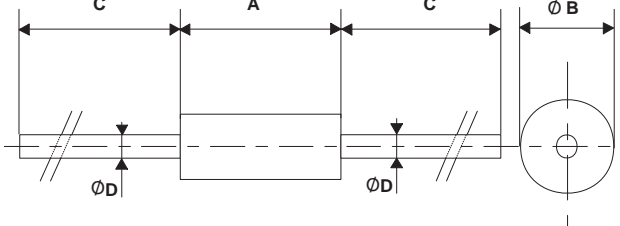


**Fig. 9:** Relative variations of dynamic parameters versus junction temperature.



**PACKAGE MECHANICAL DATA**  
DO-41

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.1	5.20	0.160	0.205
B	2	2.71	0.080	0.107
C	25.4		1	
D	0.712	0.863	0.028	0.034



Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH102	STTH102	DO-41	0.34 g	2000	Ammopack
STTH102RL	STTH102	DO-41	0.34 g	5000	Tape & reel

- Cooling method: by conduction (method A)
- Epoxy meets UL 94,V0

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